612-455-3801

Date Mailed: April 18, 2006

Shoot 1 of 1

FORM 1449*	INFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1420US01	Application Number: 10/804,610			
İ	in an application		Applicant: KITAOKA, et al.			
	(Use several shoots if necessary)	Filing Date: March 18, 2004	Group Art Unit; 2818			

		U.S. 1	PATENT DOCUMEN	TS			
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING IF APPRO	DATE
TH	6,121,121	September, 2000	Koids	438	481		
	6,503,610	January, 2003	Hiramatsu, et al.	428	210		
	6.667,252	Documber, 2003	Miyajima, et al.	438	796	-	
V	2005/0082564	April, 2005	Kitzoka, et al.	257	103		
						·	
		FOREIG	n patent docum	ENTS			
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
				<u> </u>		YES	NO
TH	3409576	March, 2003	Jepan			Abstract	
TH	2000-357663	December, 20003	Japan			Abstract	
	OTUF	DOCUMENTS (h	cheding Author Tide	Orte Bestings	base Etc.)		
TH	OTHER DOCUMENTS (Including Author, Title, Oste, Pertinent Pages, Etc.) Kawamura, et al., "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE)Technique", Jpn. J. Appl. Phys., vol. 42, part 2, no. 1A/B, January 15, 2003, pp. L4-L6						
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EXAMINER	/Tu Tu Ho/ (06/16/2	06) DATE CONSIDERED	06/16/2006				
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.							